

Product brief

GaN EiceDRIVER™ family

Single-channel isolated gate driver ICs for high voltage GaN switches

CoolGaN™ e-mode HEMTs are best driven by Infineon's EiceDRIVER™ ICs, the 1EDF5673K, 1EDF5673F and 1EDS5663H. They ensure robust and highly efficient high voltage GaN switch operation whilst concurrently minimizing R&D efforts and shortening time-to-market.

Key advantages of designing with the GaN $\mathsf{EiceDRIVER}^{\mathsf{m}}$ family

Positive and negative gate drive currents:

> Fast turn-on / turn-off GaN switch slew-rates

Firmly hold gate voltage at zero, during off-phase:

- > Avoids spurious GaN switch turn-on
- > Up to 50% lower dead-time losses

Configurable and constant GaN switching slew-rates, across wide range of switching frequency and duty-cycle:

- > Robust and energy efficient SMPS designs
- > Short time-to-market

Integrated galvanic isolation:

- > Robust operation in hard-switching applications
- > Safe isolation where needed

GaN EiceDRIVER[™] ICs evaluation environment High frequency (1 MHz) half-bridge evaluation board EVAL_1EDF_G1_HB_GAN

Key components:

- > GaN switches: 2x CoolGaN[™] 600 V e-mode HEMTs (IGOT60R070D1)
- > GaN drivers: 2x GaN EiceDRIVER™ (1EDF5673K)

Order code: EVAL_1EDF_G1_HB_GAN*

*Coming soon

Server Datacom DCJCC Charger Charger Charging Ch

Key use cases

- > Totem-pole PFCs
- > Vienna rectifiers
- > Multi-level topologies
- > Resonant LLC

Key features

- Low ohmic outputs: Source: 0.85 Ω
 Sink: 0.35 Ω
- Single-channel galvanic isolation:
 Functional: V_{IO}= 1500 V_{DC}
 - V_{IOWM} = 510 V_{rms} (16-pin DSO)
 - $V_{IOWM} = 460 V_{rms}$ (LGA 5x5) Reinforced: $V_{IOTM} = 8000 V_{pk}$ (VDE 0884-10 pending)

V_{IOWM} = 1420 V_{DC}

- CMTI min: 200 V/ns
- > Timing:

Minimum output pulse width: 18 ns Propagation delay accuracy: 13 ns



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High power SMPS application example



*GaN EiceDRIVER™ ICs are single-channel products

Product portfolio

Package	13-pin LGA 5x5 mm	16-pin DSO 150 mil	16-pin DSO 300 mil
Product	1EDF5673K*	1EDF5673F	1EDS5663H
OPN	1EDF5673KXUMA1	1EDF5673FXUMA1	1EDS5663HXUMA1
Isolation (input to output)	$V_{IO} = 1500 V_{DC}$	V _{IO} = 1500 V _{DC}	V _{IOTM} = 8000 V _{pk} (VDE0884-10 pending)
Source/sink output resistance	0.85 Ω /0.35 Ω	0.85 Ω /0.35 Ω	0.85 Ω /0.35 Ω
UVLO	4.5 V / 5.0 V	4.5 V / 5.0 V	4.5 V / 5.0 V

*Coming soon

www.infineon.com/gan-eicedriver

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